# QA tests of the CBM Silicon Tracking System sensors with an infrared laser

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### Introduction

#### Silicon Tracker System design:

- Detector acceptance
  - rapidities from centre-of-mass to beampipe
  - ▶ angular coverage  $2.5^{\circ} < \Theta < 25.0^{\circ}$
- Low mass large area detector
  - readout electronics away from the acceptance
  - ▶ double sided 300 µm thick silicon sensors (8 stations)
  - material budget  $\simeq 1\% X_0/\text{station}$
  - low scattering, high momentum resolution
  - track matching in MVD and RICH/MUCH



• See A. Lymanets, Mo HK15 talk for more details



- $\Delta p/p \simeq 1.5\%$
- up to  $\simeq 25\,\mu m$  single hit resolution

### Microstrip sensor prototypes

- Double-sided n-type silicon sensors
  - ▶  $58\,\mu{
    m m}$  pitch
  - ▶ 1024 strips per sensor
  - AC-coupling, aluminium strips
  - 7.5° stereo angle for p-side (suppression of the ghost track rate)
- Sensor inside a sandwich PCB frame:





- $\bullet~$  radiation tolerance up to  $10^{14}\,n_{\rm eq}/cm^2$
- signal transfer to r/o electronics by microcable (polyimide  $10 \,\mu\text{m}$ , aluminium  $14 \,\mu\text{m}$  thick)

# Charge collection in the sensor medium interaction with MIP

- MIP (Minimum Ionising Particle) penetrates silicon sensor
- Deposited charge drifts along  $\vec{E}$  field to the electrodes



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- $\Delta E = 3.79 \pm 0.01 \,\mathrm{eV}$  per one e-h pair got from
  - [C. Bussolati et al. Phys. Rev. 136, A1756]
- $\Delta_p$  is found for 300  $\mu {
  m m}$  silicon
- $\Delta_p \simeq 23 \times 10^3$
- this value depends on many input parameters



# Charge collection in the sensor medium

interaction with (infra)red laser

 $\simeq 300 \, \mu \mathrm{m}$ 

- (Infra)red laser can be used to mimic MIPs
- Deposited charge drifts along  $\vec{E}$  field to the electrodes

 $58 \,\mu m$ 



• Silicon absorption depth

[Green MA, Keevers MJ. 1995;3:189 - 192.]

▶ red light (660 nm)

 $4\,\mu\mathrm{m}$ 

▶ infrared light (1060 nm) 901 µm

# Charge collection in the sensor medium

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- Laser:
  - ▶ infrared 1060 nm
  - triggered by external puls generator
- Focuser:
  - focusing distance  $10 \pm 1 \,\mathrm{mm}$
  - beam size  $12 \pm 2 \,\mu \mathrm{m}$
- Step motor
  - controlled by EPICS
  - $\blacktriangleright$  positioning precision  $\simeq 1\,\mu{\rm m}$
- Data acquisition
  - DABC over optical channel (ver. 2012)
  - GO4 online monitoring

#### Laser test stand

- Constructed for studies of the sensor properties with a laser
- Sensor + readout + laser in a light tight box
- Readout controllers additionally shielded





#### Laser test stand scheme



### External triggering system



### Positioning system



• Vertiacal positioning is manual



- Automated X/Y positioning
- $\bullet~{\rm Accuracy}~{\rm up}~{\rm to}~1\,\mu{\rm m}$
- Scanning along predefined pattern with EPICs based software

### Online monitor and data processing



- Charge sharing between neighbouring strips
- Focusing is complicated with manual z-positioning
- External trigger forces to r/o all 128 channels per pulse

### Conclusions and outlook

- Infrared laser is a good tool to test silicon sensor prototypes
- Red laser may be used for cross-check/surface effect studies
- Laser test stand is ready for operation
- Application of the external triggering allows go deep below the noise

Things we still missing:

- Motorised z-positioning for the focusing purposes
- Online feed-back from data stream for the pattern correction:
  - misalignment correction
  - automatic focusing
- Remote control for hardware components: bias voltage, pulse generator...
- Automatise the procedure for the QA during the mass production

![](_page_12_Picture_12.jpeg)